# Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

#### **Features**

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays of 12 V Rail
- Capable of Driving Relay Coils Rated up to 6.0 W at 12 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V<sub>DS(ON)</sub> Reduces System Current Drain
- These are Pb-Free Devices

#### **Typical Applications**

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers



### ON Semiconductor®

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#### MARKING DIAGRAMS



SOT-23 CASE 318 STYLE 21



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SC-74 CASE 318F STYLE 7



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

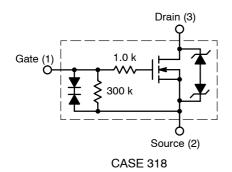
(Note: Microdot may be in either location)

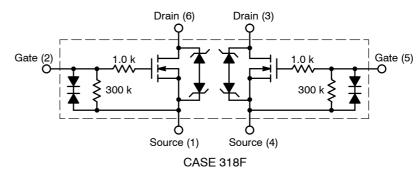
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### **INTERNAL CIRCUIT DIAGRAMS**





# **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Symbol	Rating		Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage – Continuous		14	$V_{dc}$
V <sub>GS</sub>	Gate to Source Voltage – Continuous		6	V <sub>dc</sub>
I <sub>D</sub>	Drain Current – Continuous		500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (T <sub>Jinitial</sub> = 25°C)		50	mJ
$T_J$	Junction Temperature		150	°C
T <sub>A</sub>	Operating Ambient Temperature		-40 to 85	°C
T <sub>stg</sub>	Storage Temperature Range		-65 to +150	°C
P <sub>D</sub>	Total Power Dissipation (Note 1) Derating Above 25°C	SOT-23	225 1.8	mW mW/°C
P <sub>D</sub>	Total Power Dissipation (Note 1) Derating Above 25°C	SC-74	380 3.0	mW mW/°C
$R_{ hetaJA}$	Thermal Resistance Junction-to-Ambient (Note 1)	SOT-23 SC-74	556 329	°C/W
ESD	Human Body Model (HBM) According to EIA/JESD22/A114		2000	V

<sup>1.</sup> Mounted onto minimum pad board.

# TYPICAL ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit			
OFF CHAR	OFF CHARACTERISTICS							
V <sub>BRDSS</sub>	Drain to Source Sustaining Voltage (Internally Clamped) (ID = 10 mA)	14	16	17	V			
B <sub>VGSO</sub>	I <sub>g</sub> = 1.0 mA	-	-	8	٧			
I <sub>DSS</sub>	Drain to Source Leakage Current $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_A = 25^{\circ}\text{C})$ $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_A = 85^{\circ}\text{C})$	- -	- -	20 40	μΑ			
I <sub>GSS</sub>	Gate Body Leakage Current $(V_{GS} = 3.0 \text{ V}, V_{DS} = 0 \text{ V})$ $(V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V})$	- -	- -	35 65	μΑ			
ON CHARA	CTERISTICS	•	•					
V <sub>GS(th)</sub>	Gate Threshold Voltage $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}) $ $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_A = 85^{\circ}\text{C}) $	0.8 0.8	1.2 -	1.4 1.4	V			
R <sub>DS(on)</sub>	$\begin{array}{l} \text{Drain to Source On-Resistance} \\ (I_D = 250 \text{ mA}, \text{ V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}, \text{ T}_A = 85^{\circ}\text{C}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}, \text{ T}_A = 85^{\circ}\text{C}) \end{array}$	- - - -	- - - -	1.2 1.3 0.9 1.3 0.9	Ω			
I <sub>DS(on)</sub>	Output Continuous Current $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V})$ $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_{A} = 85^{\circ}\text{C})$		400 -	-	mA			
9FS	Forward Transconductance (V <sub>OUT</sub> = 12.0 V, I <sub>OUT</sub> = 0.25 A)		490	-	mmhos			

# TYPICAL ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit		
DYNAMIC CHARACTERISTICS							
C <sub>iss</sub>	Input Capacitance (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 10 kHz)	-	23	_	pF		
C <sub>oss</sub>	Output Capacitance (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 10 kHz)	_	30	-	pF		
C <sub>rss</sub>	Transfer Capacitance $(V_{DS} = 12.0 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	-	7	_	pF		

#### **SWITCHING CHARACTERISTICS**

Symbol	Characteristic	Min	Тур	Max	Units
t <sub>PHL</sub>	Propagation Delay Times: High to Low Propagation Delay; Figure 1 ( $V_{DS}$ = 12 V, $V_{GS}$ = 5.0 V) Low to High Propagation Delay; Figure 1 ( $V_{DS}$ = 12 V, $V_{GS}$ = 5.0 V)	- -	21 91	- -	nS
t <sub>f</sub> t <sub>r</sub>	Transition Times: Fall Time; Figure 1 ( $V_{DS}$ = 12 V, $V_{GS}$ = 5.0 V) Rise Time; Figure 1 ( $V_{DS}$ = 12 V, $V_{GS}$ = 5.0 V)	- -	36 61	- -	nS

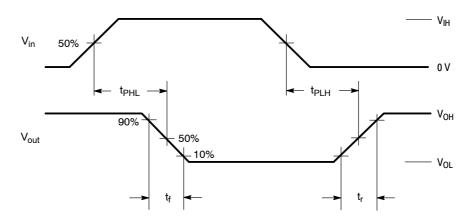


Figure 1. Switching Waveforms

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise specified)

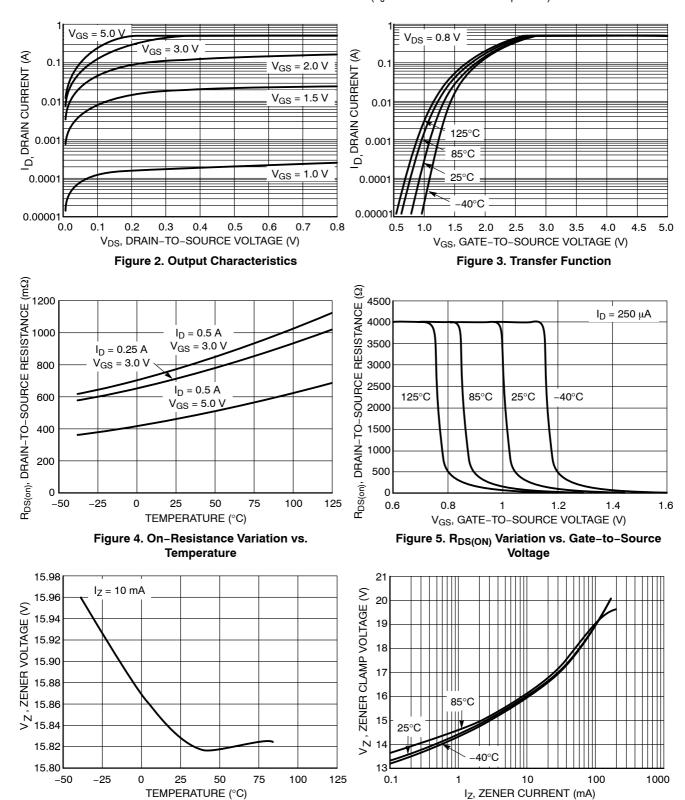
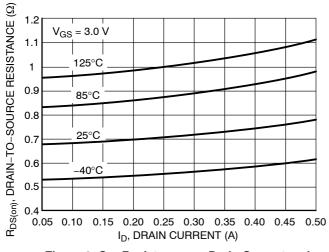


Figure 6. Zener Voltage vs. Temperature

Figure 7. Zener Clamp Voltage vs. Zener Current

# $\textbf{TYPICAL PERFORMANCE CURVES} \ (T_J = 25^{\circ}C \ unless \ otherwise \ specified)$



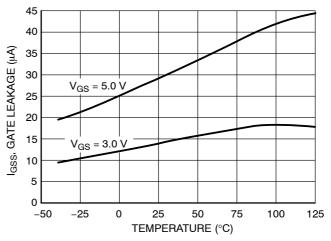


Figure 8. On-Resistance vs. Drain Current and Temperature

Figure 9. Gate Leakage vs. Temperature

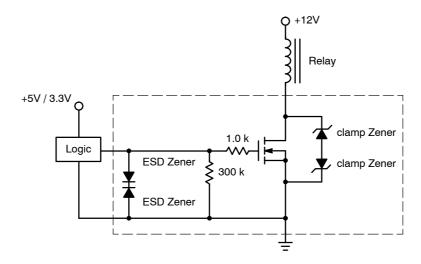
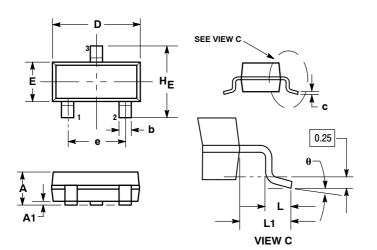


Figure 10. Typical Application Circuit

#### **PACKAGE DIMENSIONS**

#### SOT-23 (TO-236) CASE 318-08 **ISSUE AP**

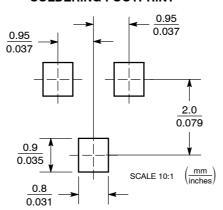


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN

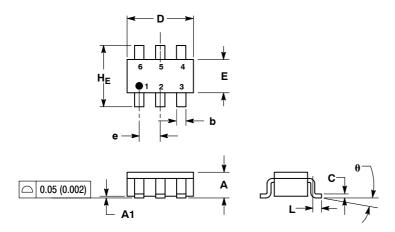
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### SC-74 CASE 318F-05 ISSUE M



#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES
  LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 318F-01, -02, -03, -04 OBSOLETE. NEW
- STANDARD 318F-05

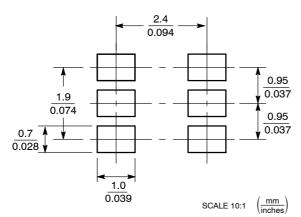
	М	ILLIMETE	ETERS INCHES				
DIM	MIN	NOM	MAX	MIN NOM MAX			
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
С	0.10	0.18	0.26	0.004	0.004 0.007		
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008 0.016 0.0		0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ	0°	_	10°	0°	-	10°	

#### STYLE 7:

- PIN 1. SOURCE 1 2. GATE 1
  - 3.

  - 6. DRAIN
- - DRAIN 2 SOURCE 2
  - GATE 2

#### **SOLDERING FOOTPRINT\***



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